PCI	N Num	ber:	20	20201202000.2					PCN Date: Dec 7, 2020			
Titl	le:	Qualification	of A	IZU	ZU as an additional Fab Site option for select CMOS9T devices							
Cus	stomer	Contact:		PC	<u>N Manager</u>		Dept:		Qua	lity Services		
Pro	posed	1 st Ship Date		Jur	n 7, 2021	Estimated Availabilit		le		e provided at ple request.		
Cha	ange Ty	уре:										
	Assem	nbly Site		Assembly Process					Asseml	oly Materials		
	Design	า			Electrical Spe	ecification			Mechar	nical Specification		
	Test S	ite			Packing/Ship	ping/Labelir	ıg		Test Process			
	Wafer	Bump Site			Wafer Bump	Material			Wafer I	Bump Process		
\boxtimes	Wafer	Fab Site		Wafer Fab Materials					Wafer I	Fab Process		
		·		Part number change								
	<u> </u>				DCN	Dataila				•		

PCN Details

Description of Change:

Texas Instruments is pleased to announce the qualification of its AIZU fabrication facility as an additional Wafer Fab source for the selected devices listed in "Product Affected" section.

	Current Sites		Additional Sites					
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter			
MAINEFAB	CMOS9T	200mm	AIZU	CMOS9T	200mm			

Qual details are provided in the Qual Data Section.

Reason for Change:

Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Current

Chip Site	Chip Site Origin (20L)	Chip Site Country Code (21L)	Chip Site City
MAINEFAB	CUA	USA	South Portland

New Fab Site

Chip Site	Chip Site Origin (20L)	Chip Site Country Code (21L)	Chip Site City
AIZU	CU2	JPN	Aizuwakamatsu-shi

Sample product shipping label (not actual product label)



LBL: 5A (L)T0:1750



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T) LOT: 3959047MLA (4W) TKY (1T) 7523483\$12 (P) (2P) REV: (20L) CSO: SHE (22L) ASO: MLA (23L) ACO: MYS

Product Affected:

LP5907QMFX-1.2Q1	LP5907QMFX-2.5Q1	LP5907QMFX-3.0Q1	LP5907QMFX-3.8Q1
LP5907QMFX-1.8Q1	LP5907QMFX-2.8Q1	LP5907QMFX-3.3Q1	LP5907QMFX-4.5Q1

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Offload: LP5907AZ (CMOS9T): Aizu Fab (From MFAB) DBV at TIEM Q100 Grade1

Approved October 16, 2019

Product Attributes

Attributes	Qual Device: LP5907QMFX-1.2Q1	Qual Device: LP5907QMFX-1.8Q1	Qual Device: LP5907QMFX-2.5Q1	Qual Device: LP5907QMFX-2.8Q1	Qual Device: LP5907QMFX-3.0Q1	Qual Device: LP5907QMFX-3.3Q1	Qual Device: LP5907QMFX-3.8Q1
Automotive Grade Level	Grade 1						
Operating Temp Range	-40 to +125 C						
Product Function	Power Management						
Die Attributes	-	-	-	-	-	-	-
Wafer Process ID	CMOS9T						
Package Attributes	-	-	-	-	-	-	-
Assembly Site	TIEM-AT	TIEM-AT	TIEM-AT	TIEM-AT	TIEM-AT	TIEM	TIEM
Package Type	SOT-23						
Package Designator	DBV						
Ball/Lead Count	5	5	5	5	5	5	5
Flammability Rating	UL 94 V-0						

Product Attributes

Attributes	Qual Device: <u>LP5907QMFX</u> - <u>4.5Q1</u>	QBS Process Reference: BQ76PL455APFC-Q1	QBS Process Reference: LDC1612QDNTQ1	QBS Process Reference: LDC1614QRGHRQ1	QBS Product/Process Reference LP5907xxQDQNRQ1	QBS Package Reference: LM4128AQ1MF- 4.1	QBS Package Reference: <u>LP5907QMFX-</u> <u>4.5Q1</u>
Automotive Grade Level	Grade 1	Grade 2	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +105 C	-40 to +125 C	-40 to +125 C	-40 to +125 C	-40 to +125 C	-40 to +125 C
Product Function	Power Management	Power Management	Signal Chain	Signal Chain	Power Management	Power Management	Power Management
Die Attributes	-	-		-		-	-
Wafer Process ID	CMOS9T	CMOS9T, VIP50CLZ3	CMOS 9T	CMOS 9T	CMOS 9T	CMOS CS65	CMOS9T
Package Attributes	-	-	-	-		-	-
Assembly Site	TIEM	TITL (TAI)	TIEM	TIEM	Hana	TIEM	TIEM
Package Type	SOT-23	TQFP	WSON	WQFN	uQFN	SOT23	SOT-23
Package Designator	DBV	PFC	DNT	RGH	DQN	DBV	DBV
Ball/Lead Count	5	80	12	16	4	5	5
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0

- QBS: Qual By Similarity Qual Device LP5907QMFX-3.8Q1 is qualified at LEVEL1-260C
- Qual Device LP5907QMFX-1.2Q1 is qualified at LEVEL1-260C
 Qual Device LP5907QMFX-2.8Q1 is qualified at LEVEL1-260C
- Qual Device LP5907QMFX-3.0Q1 is qualified at LEVEL1-260C
 Qual Device LP5907QMFX-3.3Q1 is qualified at LEVEL1-260C
- Qual Device LP5907QMFX-4.5Q1 is qualified at LEVEL1-260C
- Qual Device LP5907QMFX-1.8Q1 is qualified at LEVEL1-260CG
- Qual Device LP5907QMFX-2.5Q1 is qualified at LEVEL1-260C

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Mi n Lot Qt y	SS/Lo t	Test Name / Condition	Duration	Qual Device: <u>LP5907QMFX</u> -1.2Q1	Qual Device: <u>LP5907QMFX</u> -1.8Q1	Qual Device: <u>LP5907QMFX</u> -2.5Q1	Qual Device: <u>LP5907QMFX</u> -2.8Q1	Qual Device: <u>LP5907QMFX</u> -3.0Q1	Qual Device: <u>LP5907QMFX</u> -3.3Q1	Qual Device: <u>LP5907QMFX</u> -3.8Q1
	Test	Group A -	- Accel	lerated E	nvironment Stress	s Tests							
PTC	A 5	JEDEC JESD22 -A105	1	45	Power Temperature Cycle	1000 Cycles	N/A						
	Test	Group B -	- Acce	lerated L	ifetime Simulation	Tests							
	Te		C – Pac	ckage As	sembly Integrity 1	ests							
SBS	C 5	AEC Q100- 010	3	50	Solder Ball Shear (Cpk>1.67)	Post HTSL/Bump	N/A for Package						
SBS	C 5	AEC Q100- 010	3	50	Solder Ball Shear (Cpk>1.67)	Solder Balls	N/A for Package						
	Т	est Group	D – Di	ie Fabrica	ation Reliability To	ests							
EM	D 1	JESD61	-	-	Electromigratio n	-	Completed Per Process Technology Requirement s						
TDD B	D 2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirement s						
HCI	D 3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirement s	Completed Per Process Technology Requirement					
NBTI	D 4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirement s						

Туре	#	Test Spec	Mi n Lot Qt y	SS/Lo t	Test Name / Condition	Duration	Qual Device: <u>LP5907QMFX</u> -1.2Q1	Qual Device: <u>LP5907QMFX</u> -1.8Q1	Qual Device: <u>LP5907QMFX</u> -2.5Q1	Qual Device: <u>LP5907QMFX</u> -2.8Q1	Qual Device: <u>LP5907QMFX</u> -3.0Q1	Qual Device: <u>LP5907QMFX</u> -3.3Q1	Qual Device: <u>LP5907QMFX</u> -3.8Q1
SM	D 5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirement S						
		Test Grou	ıр Е –	Electrical	Verification Test	ts							
НВМ	E 2	AEC Q100- 002	1	3	ESD - HBM - Q100	1000 V	1/3/0	-	-	-	-	1/3/0	-
НВМ	E 2	AEC Q100- 002	1	3	ESD - HBM - Q100	1500 V	1/3/0	-	-	-	-	1/3/0	-
НВМ	E 2	AEC Q100- 002	1	3	ESD - HBM - Q100	2000 V	1/3/0	-	-	-	-	1/3/0	-
НВМ	E 2	AEC Q100- 002	1	3	ESD - HBM - Q100	2500 V	1/3/0	-	-	-	-	1/3/0	-
НВМ	E 2	AEC Q100- 002	1	3	ESD - HBM - Q100	3000 V	1/3/0	-	-	-	-	1/3/0	-
НВМ	E 2	AEC Q100- 002	1	3	ESD - HBM - Q100	4000 V	1/3/0	-	-	-	-	1/3/0	-
НВМ	E 2	AEC Q100- 002	1	3	ESD - HBM - Q100	500 V	1/3/0	-	-	-	-	1/3/0	-
CDM	E 3	AEC Q100- 011	1	3	ESD - CDM - Q100	1000 V	1/3/0	-	-	-	-	1/3/0	-
CDM	E 3	AEC Q100- 011	1	3	ESD - CDM - Q100	1500 V	1/3/0	-	-	-	-	1/3/0	-
CDM	E 3	AEC Q100- 011	1	3	ESD - CDM - Q100	250 V	1/3/0	-	-	-	-	1/3/0	-
CDM	E 3	AEC Q100-	1	3	ESD - CDM - Q100	500 V	1/3/0	-	-	-	-	1/3/0	-

Туре	#	Test Spec	Mi n Lot Qt y	SS/Lo t	Test Name / Condition	Duration	Qual Device: <u>LP5907QMFX</u> -1.2Q1	Qual Device: <u>LP5907QMFX</u> -1.8Q1	Qual Device: <u>LP5907QMFX</u> -2.5Q1	Qual Device: <u>LP5907QMFX</u> -2.8Q1	Qual Device: <u>LP5907QMFX</u> -3.0Q1	Qual Device: <u>LP5907QMFX</u> -3.3Q1	Qual Device: <u>LP5907QMFX</u> -3.8Q1
		011											
CDM	E 3	AEC Q100- 011	1	3	ESD - CDM - Q100	750 V	1/3/0	-	-	-	-	1/3/0	-
LU	E 4	AEC Q100- 004	1	6	Latch-up	Latchup/125c	1/6/0	-	-	-	-	-	-
ED	E 5	AEC Q100- 009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Tyj e	,	Test Spec	Mi n Lo t Qt y	SS/L ot	Test Name / Condition	Duration	Qual Device: <u>LP5907QMF</u> X-4.5Q1	QBS Process Reference: BQ76PL455AP FC-Q1	QBS Process Reference: LDC1612QDN TQ1	QBS Process Reference: LDC1614QRGH RQ1	QBS Product/Process Reference LP5907xxQDQN RQ1	QBS Package Reference: <u>LM4128AQ1</u> <u>MF-4.1</u>	QBS Package Reference : LP5907QM FX-4.5Q1
	Test (Accele	rated Er	vironment Stre	ss Tests							
PC	, A	JEDEC J-STD- 020 JESD2 2-A113	3	77	Automotive Preconditioni ng Level 1	3X IR REFLOW/260 C+5 / -0C	1/160/0	-	-	3/693/0		3/893/0	1/392/0
PC	, A 1	JEDEC J-STD- 020 JESD2 2-A113	3	77	Automotive Preconditioni ng Level 3	Auto Precon L3/260	-	1/270/0	4/770/0	-		-	-
HA T	S A	JEDEC JESD2 2-A110	3	77	Biased HAST, 110C/85%RH	264 hours	-	1/77/0	-	-		-	-
HA:	S A	JEDEC JESD2 2-A110	3	77	Biased HAST, 130C/85%RH	96HRS	1/77/0	-	3/231/0	3/231/0		3/231/0	1/160/0
AC	A 3	JEDEC JESD2 2-A102	3	77	Autoclave 121C	96HRS	1/77/0	1/77/0	3/231/0	3/231/0		3/231/0	1/77/0
то	A 4	JEDEC JESD2 2-A104 and Append ix 3	3	77	Temperature Cycle, - 65/150C	500CYC	1/77/0	1/77/0	3/231/0	3/231/0		3/231/0	1/77/0
TC WB		MIL- STD88 3 Method 2011	1	30	Auto Post TC Bond Pull	per MIL-STD 883 Method 2011	1/30/0	1/30/0	1/30/0	1/30/0		1/Pass	1/30/0
PT	C A 5	JEDEC JESD2	1	45	Power Temperature	1000 Cycles	N/A	-	-	-		-	-

Typ e	#	Test Spec	Mi n Lo t Qt y	SS/L ot	Test Name / Condition	Duration	Qual Device: <u>LP5907QMF</u> <u>X-4.5Q1</u>	QBS Process Reference: BQ76PL455AP FC-Q1	QBS Process Reference: LDC1612QDN TQ1	QBS Process Reference: LDC1614QRGH RQ1	QBS Product/Process Reference LP5907xxQDQN RQ1	QBS Package Reference: <u>LM4128AQ1</u> <u>MF-4.1</u>	QBS Package Reference : LP5907QM FX-4.5Q1
		2-A105			Cycle								
HTS L	6 6	JEDEC JESD2 2-A103	1	45	High Temp Storage Bake 150C	1000 hours	1/77/0	-	1/77/0	1/45/0		-	-
HTS L	6	JEDEC JESD2 2-A103	1	45	High Temp Storage Bake 175C	500 hours	-	-	-	-		-	3/231/0
	Test (Group B –	Accele	erated Li	ifetime Simulatio	n Tests							
HTC L	B 1	JEDEC JESD2 2-A108	3	77	Life Test, 125C	1000HRS	1/77/0	3/231/0	3/230/0	1/77/0	2/154/0	3/231/0	2/154/0
ELF R	B 2	AEC Q100- 008	3	800	Auto Early Life Failure Rate Grade 1	150C(24 Hrs)	-	-	-	-		3/2400/0	-
ELF R	B 2	AEC Q100- 008	3	800	Early Life Failure Rate, 125C	125C (24 Hrs).	-	3/2400/0	-	-		-	-
ELF R	B 2	AEC Q100- 008	3	800	Early Life Failure Rate, 125C	48 hours	-	-	3/2400/0	-		-	2/800/0
EDR	B 3	AEC Q100- 005	3	77	NVM Endurance, Data Retention,	-	N/A	-	-	-		-	-
EDR	B 3	AEC Q100- 005	3	77	W/E Endur High Temp	W/E 100cy/125C + 150C/1000hrs.	-	3/231/0	-	-		-	-
EDR	B 3	AEC Q100- 005	3	77	W/E Endur Low Temp	W/E 100cy/ -40C + 150C/1000hrs.	-	3/231/0	-	-		-	-
EDR	3	AEC Q100- 005	3	77	W/E Endur Room Temp	W/E 100cy/25C + 150C/1000hrs.	-	3/231/0	-	-		-	-
	Tes	t Group C	– Paci	kage As:	sembly Integrity								
WB S	1	AEC Q100- 001	1	30	Auto Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk > 1.67	3/90/0	1/30/0	-	-		-	-
WB P	C 2	MIL- STD88	1	30	Bond Pull	30 Wire, 5 units min	3/90/0	1/30/0	-	-		1/Pass	-

Typ e	#	Test Spec	Mi D Lo t Qt y	SS/L ot	Test Name / Condition	Duration	Qual Device: <u>LP5907QMF</u> <u>X-4.5Q1</u>	QBS Process Reference: BQ76PL455AP FC-Q1	QBS Process Reference: LDC1612QDN TQ1	QBS Process Reference: LDC1614QRGH RQ1	Product/Process Reference LP5907xxQDQN RQ1	QBS Package Reference: LM4128AQ1 MF-4.1	QBS Package Reference : LP5907QM FX-4.5Q1
		3 Method 2011											
SD	C 3	JEDEC JESD2 2-B102	1	15	Solderability	Steam age, 8 hours; PB- Free solder	1/15/0	-	-	1/30/0	-	1/Pass	-
PD	C 4	JEDEC JESD2 2-B100 and B108	3	10	Auto Physical Dimensions	Cpk>1.67	3/30/0	-	3/Pass	3/30/0		1/Pass	-
SBS	C 5	AEC Q100- 010	3	50	Solder Ball Shear (Cpk>1.67)	Post HTSL/Bump	N/A for Package	-	-	-		-	-
SBS	C 5	AEC Q100- 010	3	50	Solder Ball Shear (Cpk>1.67)	Solder Balls	N/A for Package	-	-	-		-	-
ш	C 6	JEDEC JESD2 2-B105	1	50	Lead Pull to Destruction	To Dest./Rec.Dat a	-	1/50/0	-	-		-	-
	Tes	st Group D	– Die	Fabrica	tion Reliability 1	ests							
EM	D 1	JESD6 1	-	-	Electromigrati on	-	Completed Per Process Technology Requireme nts	-	-	-		-	-
TDD B	D 2	JESD3 5	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requireme nts	-	-	-		-	-
			Mi n				Qual	QBS	QBS	QBS Process	QBS Product/Process	QBS	QBS Package
Typ e	#	Test Spec	Lo t Qt	SS/L ot	Test Name / Condition	Duration	Device: <u>LP5907QMF</u> <u>X-4.5Q1</u>	Process Reference: BQ76PL455AP FC-Q1	Process Reference: LDC1612QDN TQ1	Reference: LDC1614QRGH RQ1	Reference LP5907xxQDQN RQ1	Package Reference: LM4128AQ1 MF-4.1	Reference : LP5907QM FX-4.5Q1
	# D 3		Lo t			Duration -	Device: LP5907QMF	Reference: BQ76PL455AP	Reference: LDC1612QDN	Reference: LDC1614QRGH	LP5907xxQDQN	Reference: LM4128AQ1	Reference : LP5907QM
е	D	JESD6 0 & 28	Lo t Qt y	ot	Condition Hot Injection	Duration -	Device: LP5907QMF X-4.5Q1 Completed Per Process Technology Requireme	Reference: BQ76PL455AP	Reference: LDC1612QDN	Reference: LDC1614QRGH	LP5907xxQDQN	Reference: LM4128AQ1	Reference : LP5907QM
HCI NBT	D 3	JESD6 0 & 28	Lo t Qt y	ot -	Hot Injection Carrier Negative Bias Temperature	-	Device: LP5907QMF X-4.501 Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme	Reference: BQ76PL455AP	Reference: LDC1612QDN	Reference: LDC1614QRGH	LP5907xxQDQN	Reference: LM4128AQ1	Reference : LP5907QM
HCI NBT	D 3 3 D 4	JESD6 0 & 28	Lo t Qt y		Hot Injection Carrier Negative Bias Temperature Instability Stress Migration	-	Device: LP5907QMF X-4.5Q1 Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme Requireme	Reference: BQ76PL455AP	Reference: LDC1612QDN	Reference: LDC1614QRGH	LP5907xxQDQN	Reference: LM4128AQ1	Reference : LP5907QM
HCI NBT I SM	D 3 3 D 4 4 D 5 5	JESD6 0 & 28 - Test Grou AEC Q100- 002 AEC	Lo t Qt y -	ot -	Hot Injection Carrier Negative Bias Temperature Instability Stress Migration Verification Te ESD - HBM - Q100	- - - 500 V	Device: LP5807OMF X-4.5Q1 Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts 1/3/0	Reference: BQ76PL455AP	Reference: LDC1612QDN	Reference: LDC1614QRGH	LP5907xxQDQN	Reference: LM4128AQ1 MF-4.1	Reference : LP5907QM FX-4.5Q1
HCI NBT I	D 3 3 D 4 D 5 E 2 E 2	JESD6 0 & 28 - Test Grou AEC Q100- 002 AEC Q100- 002	Lo t Qt y	ot -	Negative Bias Temperature Instability Stress Migration I Verification Telescope - HBM - Q100 ESD - HBM - Q100	- - sts	Device: LP5907QMF X-4.5Q1 Completed Per Process Technology Requireme nts	Reference: BQ76PL455AP	Reference: LDC1612QDN	Reference: LDC1614QRGH RQ1	LP5907xxQDQN	Reference: LM4128AQ1 MF-4.1	Reference :
HCI NBT I SM	D 3 3 D 4 D 5 E 2 E 2 E 2	JESD6 0 & 28 - Test Grou AEC Q100- 002 AEC Q100- 002 AEC AEC Q100- 002 AEC AEC Q100- 002 AEC Q100- 002	Lo t Qt y -	ot -	Negative Bias Temperature Instability Stress Migration ESD - HBM - Q100 ESD - HBM - Q100	- - - 500 V	Device: LP5807OMF X-4.5Q1 Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts 1/3/0	Reference: BQ78PL455AP FC-Q1 -	Reference: LDC1612QDN TQ1	Reference: LDC1614QRGH RQ1	LP5907xxQDQN	Reference: LM4128AQ1 MF-4.1	Reference : LP5907QM FX-4.5Q1
HCI NBT I SM HBM	D 3 3 D 4 4 D 5 E 2 E 2 E 2 E 2	JESD6 0 & 28 Test Grou AEC Q100- 002	Lo t Qt y 1 1 1	- Electrica 3	Hot Injection Carrier Negative Bias Temperature Instability Stress Migration Al Verification Te ESD - HBM - Q100 ESD - HBM - Q100 ESD - HBM -		Device: LP5907QMF X-4.5Q1 Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts 1/3/0	Reference: BQ78PL455AP FC-Q1 -	Reference: LDC1612QDN TQ1	Reference: LDC1614QRGH RQ1	LP5907xxQDQN	Reference: LM4128AQ1 MF-4.1 - - - 1/3/0	Reference : LP5907QM FX-4.5Q1
HCI NBT I SM HBM	D 3 3 D 4 D 5 E 2 2 E 2 E 2 E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E 2 C E	JESD6 0 & 28 Test Grou AEC Q100- 002	Lo t Qt y y 1 1 1 1	- Electrica 3	Hot Injection Carrier Negative Bias Temperature Instability Stress Migration at Verification Te ESD - HBM - Q100 ESD - HBM - Q100		Device: LP5907QMF X-4.5Q1 Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts 1/3/0 1/3/0	Reference: BQ78PL455AP FC-Q1 -	Reference: LDC1612QDN TQ1	Reference: LDC1614QRGH RQ1	LP5907xxQDQN	Reference: LM4128AQ1 MF-4.1	Reference : LP5907QM FX-4.5Q1
HBM HBM HBM	D 3 3 D 4 D 5 E 2 E 2 E 2 E 2 E 2 E 2 E 2 E 2 E 2 E	JESD6 0 & 28	Lo t Qt y y 1 1 1 1 1	- Electrica 3 3 3 3	Hot Injection Carrier Negative Bias Temperature Instability Stress Migration ESD - HBM - Q100		Device: LP5907QMF X-4.5Q1 Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts Completed Per Process Technology Requireme nts 1/3/0 1/3/0 1/3/0	Reference: BQ78PL455AP FC-Q1	Reference: LDC1612QDN TQ1	Reference: LDC1614QRGH RQ1	LP5907xxQDQN	Reference: LM4128AQ1 MF-4.1 - - 1/3/0 1/3/0 1/3/0 1/3/0	Reference : LP5907QM FX-4.5Q1

Typ e	#	Test Spec	Mi n Lo t Qt y	SS/L ot	Test Name / Condition	Duration	Qual Device: LP5907QMF X-4.5Q1	QBS Process Reference: BQ76PL455AP FC-Q1	QBS Process Reference: LDC1612QDN TQ1	QBS Process Reference: LDC1614QRGH RQ1	QBS Product/Process Reference LP5907xxQDQN RQ1	QBS Package Reference: <u>LM4128AQ1</u> <u>MF-4.1</u>	QBS Package Reference : LP5907QM FX-4.5Q1
CD M	E 3	AEC Q100- 011	1	3	ESD - CDM - Q100	1000 V	1/3/0	-	3/9/0	1/3/0		1/3/0	1/3/0
CD M	E 3	AEC Q100- 011	1	3	ESD - CDM - Q100	1500 V	1/3/0	-	-	-		-	1/3/0
CD M	E 3	AEC Q100- 011	1	3	ESD - CDM - Q100	250 V	1/3/0	-	-	-		-	1/3/0
CD M	E 3	AEC Q100- 011	1	3	ESD - CDM - Q100	500 V	1/3/0	-	-	-		1/3/0	1/3/0
CD M	E 3	AEC Q100- 011	1	3	ESD - CDM - Q100	750 V	1/3/0	1/3/0	-	-		1/3/0	1/3/0
LU	E 4	AEC Q100- 004	1	6	Latch-up	25C	1/6/0	1/6/0	3/18/0	1/6/0		1/6/0	1/6/0
LU	E 4	AEC Q100- 004	1	6	Latch-up	Latchup/125c	1/6/0	1/6/0	3/18/0	1/6/0		1/6/0	1/6/0
ED	E 5	AEC Q100- 009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	3/90/0	3/Pass	3/Pass	3/Pass		1/Pass	-
			Ad	ditional	Tests								
-			-	-	Auto Solderability (Pb)	>95% Lead Coverage 8 Hr Steam Age	-	-	1/Pass	-		-	-
-			1	-	Auto Solderability (Pb-Free)	>95% Lead Coverage 8 Hr Steam Age	-	-	1/Pass	-		-	-
-			•	-	Precondition Prior to HTSL	3X IR REFLOW/260 C+5 / -0C	1/80/0	-	-	-		-	-
MQ			-	-	Manufacturab ility (Auto Assembly)	(per automotive requirements)	3/Pass	1/Pass	3/Pass	3/Pass		1/Pass	-
MQ			-	-	Manufacturab ility (Wafer Fab)	(per mfg. Site specification)		1/Pass	3/Pass	-		-	-

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

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